

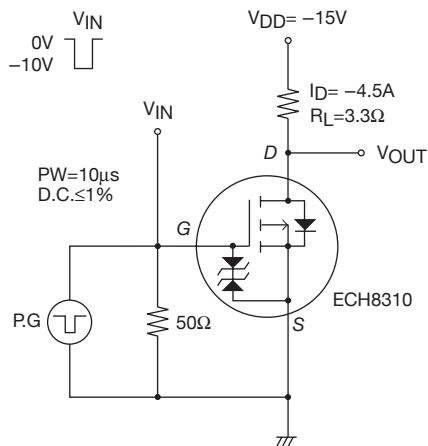
ECH8310

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0V$	-30			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30V, V_{GS} = 0V$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 16V, V_{DS} = 0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10V, I_D = -4.5A$		12		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -4.5A, V_{GS} = -10V$	9	13	17	$m\Omega$
	$R_{DS(on)2}$	$I_D = -2A, V_{GS} = -4.5V$	12	20	28	$m\Omega$
	$R_{DS(on)3}$	$I_D = -2A, V_{GS} = -4.0V$	13.5	23	32.5	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS} = -10V, f = 1MHz$		1400		pF
Output Capacitance	C_{oss}			350		pF
Reverse Transfer Capacitance	C_{rss}			250		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		10		ns
Rise Time	t_r			45		ns
Turn-OFF Delay Time	$t_{d(off)}$			134		ns
Fall Time	t_f			87		ns
Total Gate Charge	Q_g	$V_{DS} = -15V, V_{GS} = -10V, I_D = -9A$		28		nC
Gate-to-Source Charge	Q_{gs}			4		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			6		nC
Diode Forward Voltage	V_{SD}	$I_S = -9A, V_{GS} = 0V$		-0.8	-1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ECH8310-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free

